

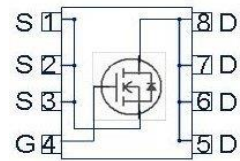
**OptiMOS™ -5 Power-Transistor**

**Product Summary**

|                  |     |    |
|------------------|-----|----|
| $V_{DS}$         | 100 | V  |
| $R_{DS(on),max}$ | 13  | mΩ |
| $I_D$            | 40  | A  |

**Features**

- OptiMOS™ - power MOSFET for automotive applications
- N-channel - Enhancement mode - Normal Level
- AEC Q101 qualified
- MSL1 up to 260°C peak reflow
- 175°C operating temperature
- Green Product (RoHS compliant)
- 100% Avalanche tested
- Feasible for automatic optical inspection (AOI)

**PG-TSDSON-8-33**


| Type            | Package        | Marking |
|-----------------|----------------|---------|
| IAUZ40N10S5N130 | PG-TSDSON-8-33 | 5N1N130 |

**Maximum ratings, at  $T_j=25\text{ °C}$ , unless otherwise specified**

| Parameter                                    | Symbol         | Conditions                                | Value        | Unit |
|--|----------------|---|--------------|------|
| Continuous drain current <sup>1)2)</sup>     | $I_D$          | $T_C=25\text{ °C}$ , $V_{GS}=10\text{V}$  | 40           | A    |
|  |                | $T_C=100\text{ °C}$ , $V_{GS}=10\text{V}$ | 35           |      |
| Pulsed drain current <sup>2)</sup>           | $I_{D,pulse}$  | $T_C=25\text{ °C}$                        | 160          |      |
| Avalanche energy, single pulse <sup>2)</sup> | $E_{AS}$       | $I_D=20\text{A}$                          | 60           | mJ   |
| Avalanche current, single pulse              | $I_{AS}$       | -   | 22           | A    |
| Gate source voltage                          | $V_{GS}$       | -   | ±20          | V    |
| Power dissipation                            | $P_{tot}$      | $T_C=25\text{ °C}$<br>$T_J=175\text{ °C}$ | 68           | W    |
| Operating and storage temperature            | $T_j, T_{stg}$ | -   | -55 ... +175 | °C   |

| Parameter                                   | Symbol     | Conditions                                   | Values |      |      | Unit |
|---|------------|--|--------|------|------|------|
|   |            |  | min.   | typ. | max. |      |
| <b>Thermal characteristics<sup>2)</sup></b> |            |  |        |      |      |      |
| Thermal resistance, junction - case         | $R_{thJC}$ | -  | -      | -    | 2.2  | K/W  |
| Thermal resistance, junction - ambient      | $R_{thJA}$ | 6 cm <sup>2</sup> cooling area <sup>3)</sup> | -      | -    | 62   |      |

**Electrical characteristics, at  $T_j=25^\circ\text{C}$ , unless otherwise specified**

**Static characteristics**

|                                  |               |  |     |      |     |               |
|----------------------------------|---------------|--|-----|------|-----|---------------|
| Drain-source breakdown voltage   | $V_{(BR)DSS}$ | $V_{GS}=0V, I_D=1\text{mA}$                          | 100 | -    | -   | V             |
| Gate threshold voltage           | $V_{GS(th)}$  | $V_{DS}=V_{GS}, I_D=27\mu\text{A}$                   | 2.2 | 3.0  | 3.8 |               |
| Zero gate voltage drain current  | $I_{DSS}$     | $V_{DS}=100V, V_{GS}=0V, T_j=25^\circ\text{C}$       | -   | -    | 1   | $\mu\text{A}$ |
|                                  |               | $V_{DS}=100V, V_{GS}=0V, T_j=125^\circ\text{C}^{2)}$ | -   | -    | 100 |               |
| Gate-source leakage current      | $I_{GSS}$     | $V_{GS}=20V, V_{DS}=0V$                              | -   | -    | 100 | nA            |
| Drain-source on-state resistance | $R_{DS(on)}$  | $V_{GS}=6V, I_D=10\text{A}$                          | -   | 14   | 17  | m $\Omega$    |
|                                  |               | $V_{GS}=10V, I_D=20\text{A}$                         | -   | 10.8 | 13  |               |
| Gate resistance <sup>2)</sup>    | $R_G$         |  | -   | 1.2  | -   | $\Omega$      |

| Parameter | Symbol | Conditions | Values |      |      | Unit |
|-----------|--------|------------|--------|------|------|------|
|           |        |            | min.   | typ. | max. |      |

**Dynamic characteristics<sup>2)</sup>**

|                              |              |   |   |      |      |    |
|------------------------------|--------------|---|---|------|------|----|
| Input capacitance            | $C_{iss}$    | $V_{GS}=0V, V_{DS}=50V,$<br>$f=1MHz$                  | - | 1173 | 1525 | pF |
| Output capacitance           | $C_{oss}$    |   | - | 197  | 256  |    |
| Reverse transfer capacitance | $C_{rss}$    |   | - | 11   | 17   |    |
| Turn-on delay time           | $t_{d(on)}$  | $V_{DD}=50V, V_{GS}=10V,$<br>$I_D=40A, R_G=3.5\Omega$ | - | 4    | -    | ns |
| Rise time                    | $t_r$        |   | - | 1    | -    |    |
| Turn-off delay time          | $t_{d(off)}$ |   | - | 6    | -    |    |
| Fall time                    | $t_f$        |   | - | 5    | -    |    |

**Gate Charge Characteristics<sup>2)</sup>**

|                       |               |   |   |     |     |    |
|-----------------------|---------------|---|---|-----|-----|----|
| Gate to source charge | $Q_{gs}$      | $V_{DD}=50V, I_D=20A,$<br>$V_{GS}=0$ to 10V | - | 5.5 | 7.2 | nC |
| Gate to drain charge  | $Q_{gd}$      |   | - | 3.7 | 6.0 |    |
| Gate charge total     | $Q_g$         |   | - | 17  | 24  |    |
| Gate plateau voltage  | $V_{plateau}$ |   | - | 4.7 | -   | V  |

**Reverse Diode**

|  |               |   |   |     |     |    |
|--|---------------|---|---|-----|-----|----|
| Diode continuous forward current <sup>2)</sup> | $I_S$         | $T_C=25^\circ C$                            | - | -   | 40  | A  |
| Diode pulse current <sup>2)</sup>              | $I_{S,pulse}$ |   | - | -   | 160 |    |
| Diode forward voltage                          | $V_{SD}$      | $V_{GS}=0V, I_F=20A,$<br>$T_j=25^\circ C$   | - | 0.9 | 1.1 | V  |
| Reverse recovery time <sup>2)</sup>            | $t_{rr}$      | $V_R=40V, I_F=40A,$<br>$di_F/dt=100A/\mu s$ | - | 40  | -   | ns |
| Reverse recovery charge <sup>2)</sup>          | $Q_{rr}$      |   | - | 39  | -   | nC |

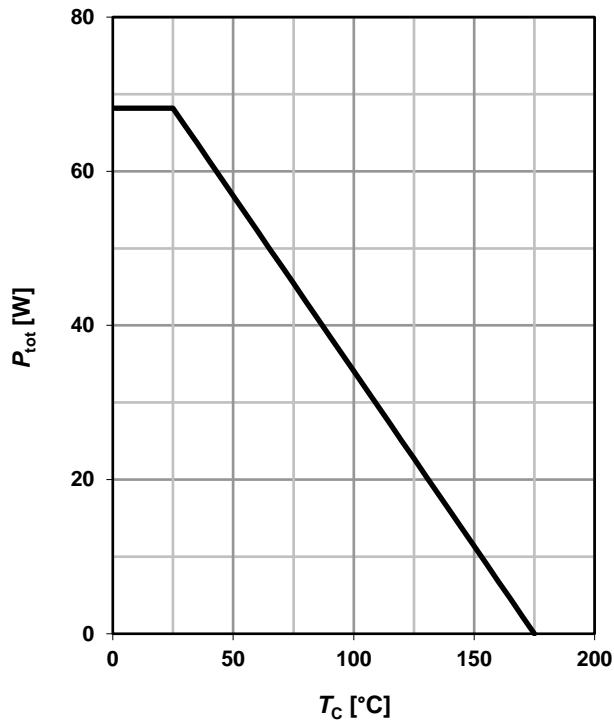
<sup>1)</sup> Current is limited by package; with an  $R_{thJC} = 2.2K/W$  the chip is able to carry 50A at 25°C.

<sup>2)</sup> The parameter is not subject to production test- verified by design/characterization.

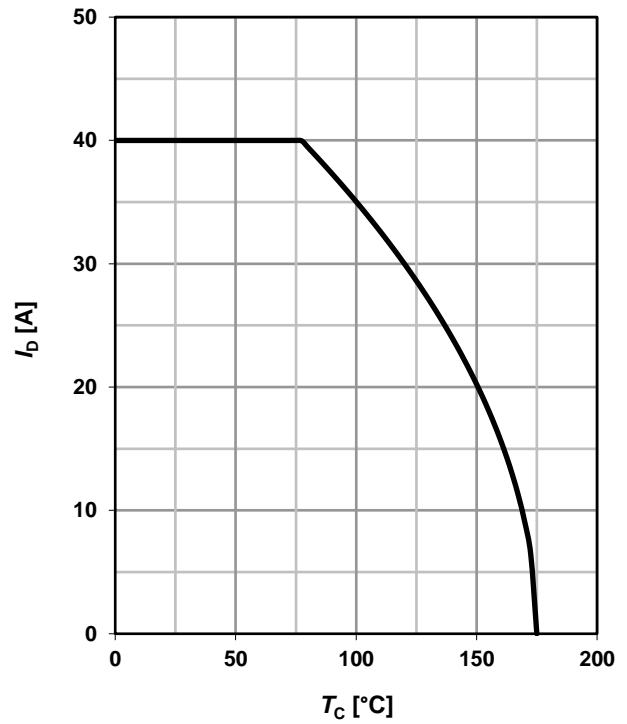
<sup>3)</sup> Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm<sup>2</sup> (one layer, 70 μm thick) copper area for drain connection. PCB is vertical in still air.

**1 Power dissipation**

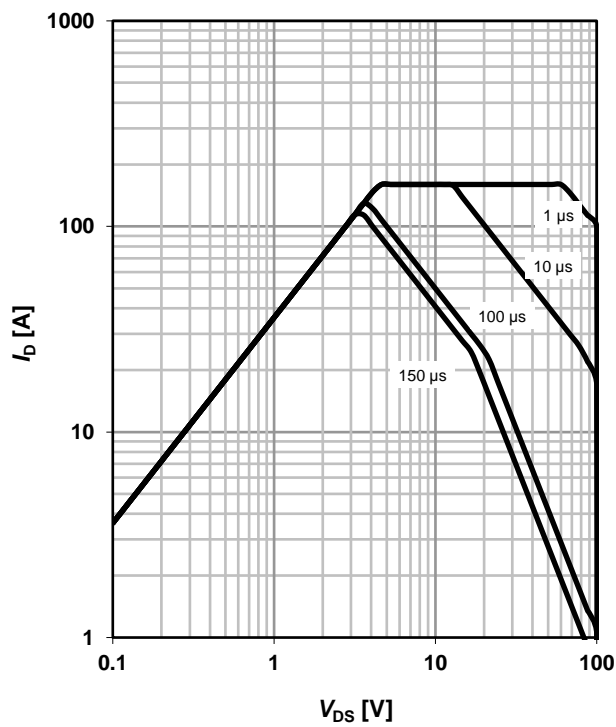
$$P_{\text{tot}} = f(T_C); V_{\text{GS}} = 10 \text{ V}$$


**2 Drain current**

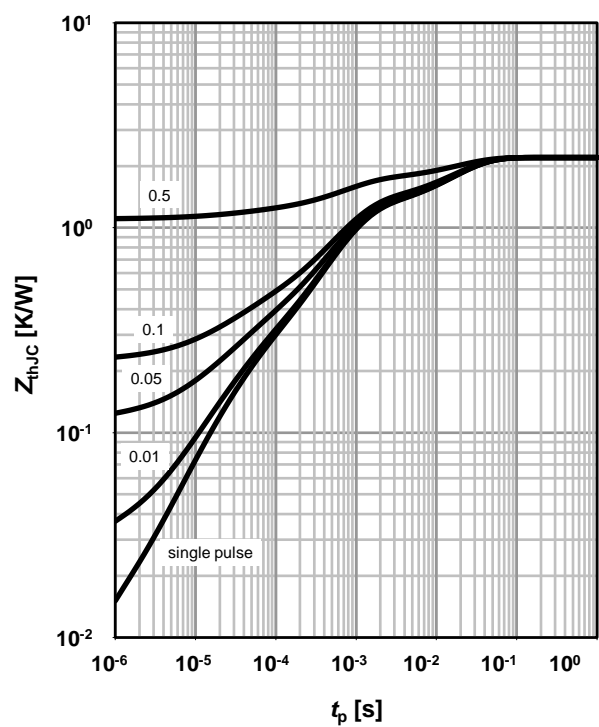
$$I_D = f(T_C); V_{\text{GS}} = 10 \text{ V}$$


**3 Safe operating area**

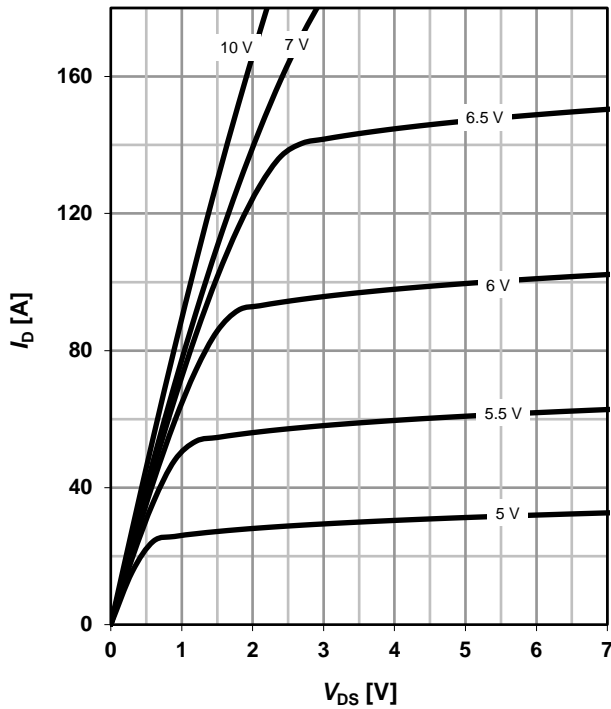
$$I_D = f(V_{\text{DS}}); T_C = 25 \text{ °C}; D = 0$$

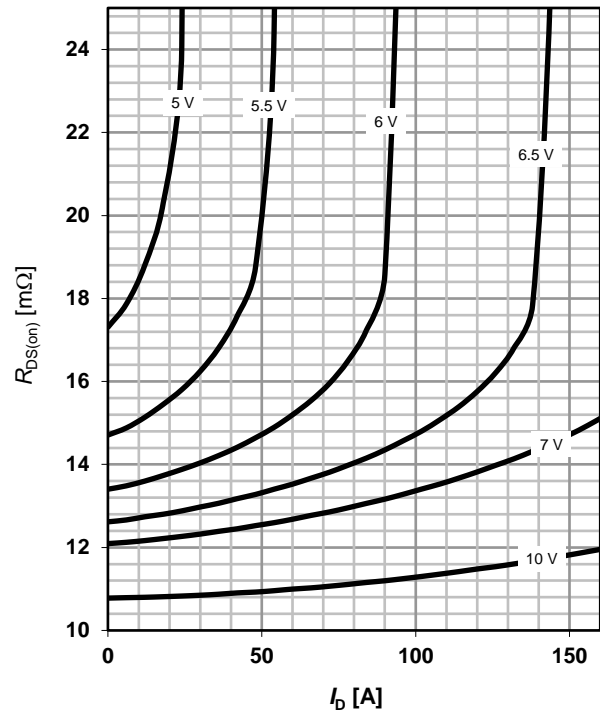
 parameter:  $t_p$ 

**4 Max. transient thermal impedance**

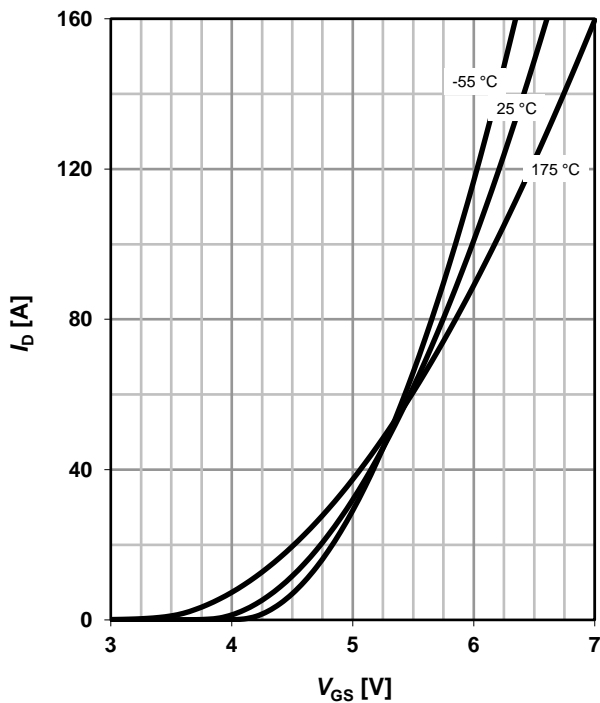
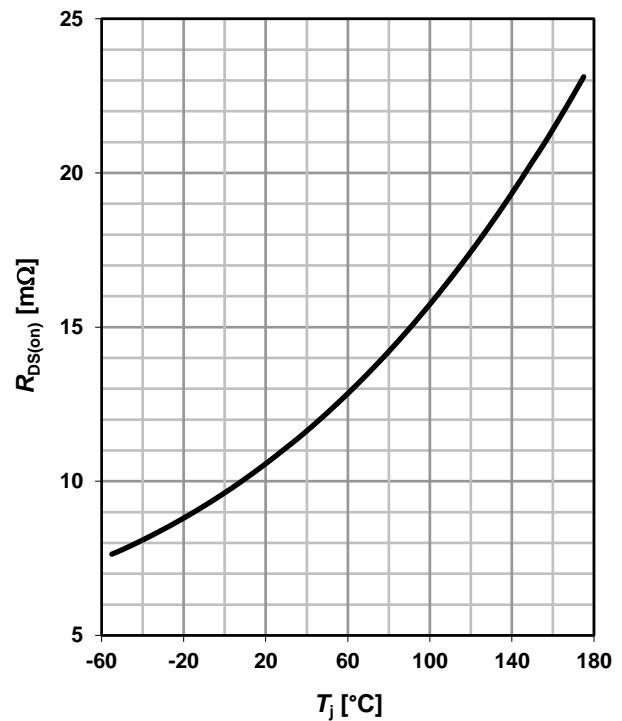
$$Z_{\text{thJC}} = f(t_p)$$

 parameter:  $D = t_p/T$ 


**5 Typ. output characteristics**
 $I_D = f(V_{DS}); T_j = 25\text{ °C}$ 

 parameter:  $V_{GS}$ 

**6 Typ. drain-source on-state resistance**
 $R_{DS(on)} = f(I_D); T_j = 25\text{ °C}$ 

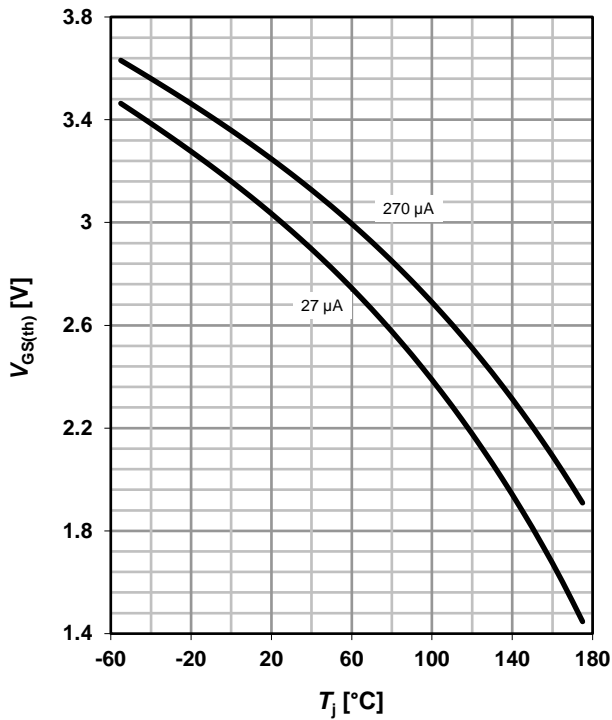
 parameter:  $V_{GS}$ 

**7 Typ. transfer characteristics**
 $I_D = f(V_{GS}); V_{DS} = 6\text{ V}$ 

 parameter:  $T_j$ 

**8 Typ. drain-source on-state resistance**
 $R_{DS(on)} = f(T_j); I_D = 20\text{ A}; V_{GS} = 10\text{ V}$ 


**9 Typ. gate threshold voltage**

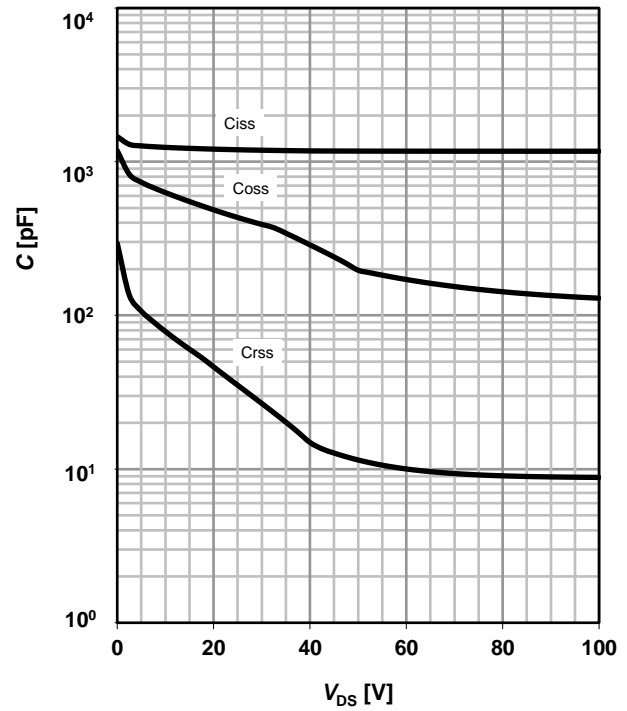
$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}$

parameter:  $I_D$



**10 Typ. capacitances**

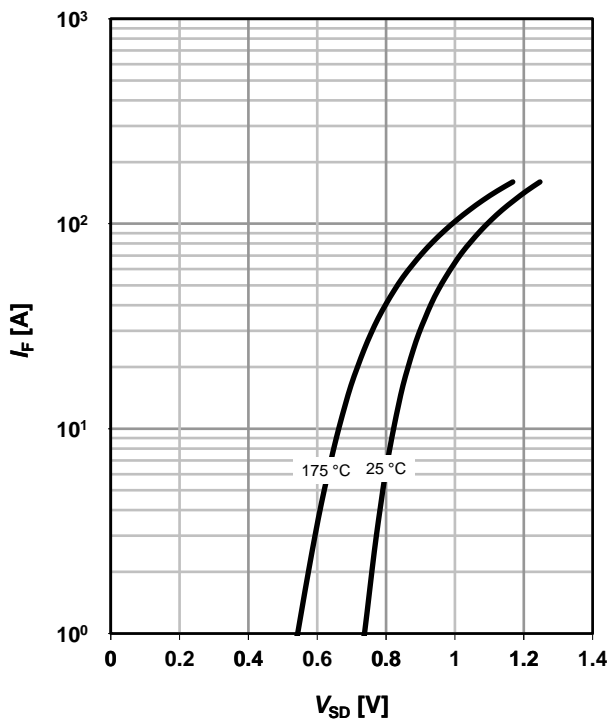
$C = f(V_{DS}); V_{GS} = 0 V; f = 1 MHz$



**11 Typical forward diode characteristics**

$I_F = f(V_{SD})$

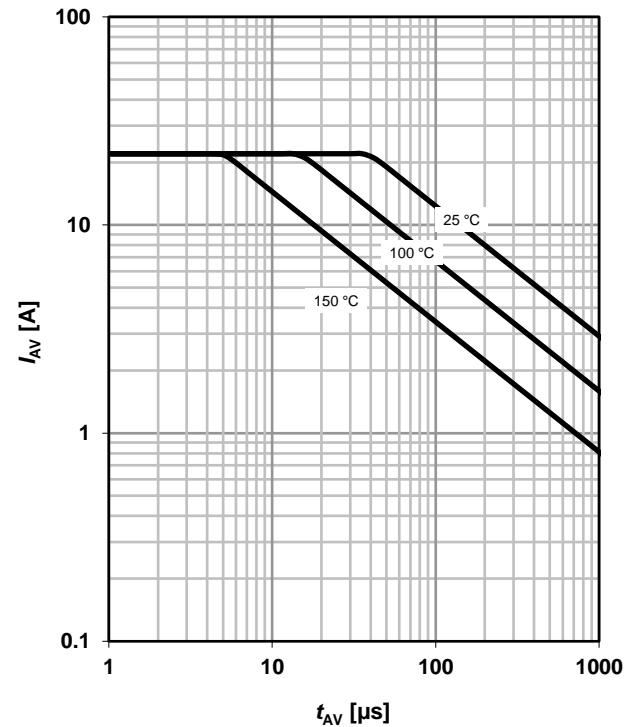
parameter:  $T_j$



**12 Avalanche characteristics**

$I_{AS} = f(t_{AV})$

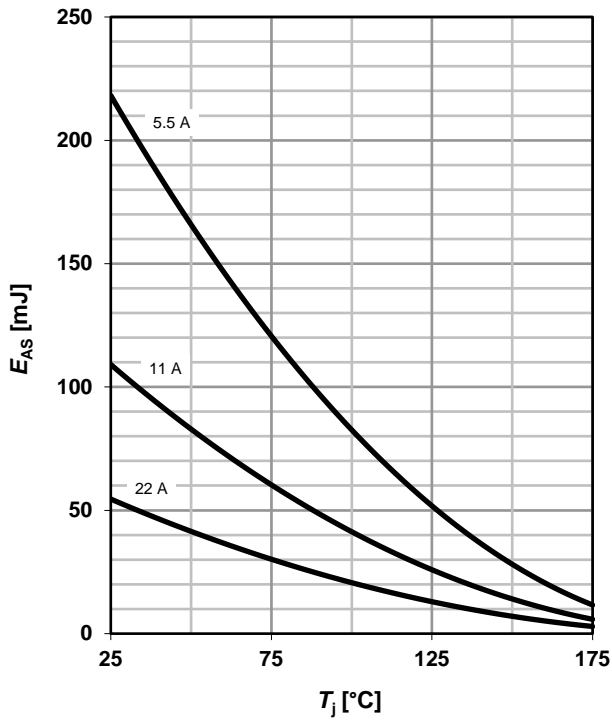
parameter:  $T_{j(start)}$



**13 Avalanche energy**

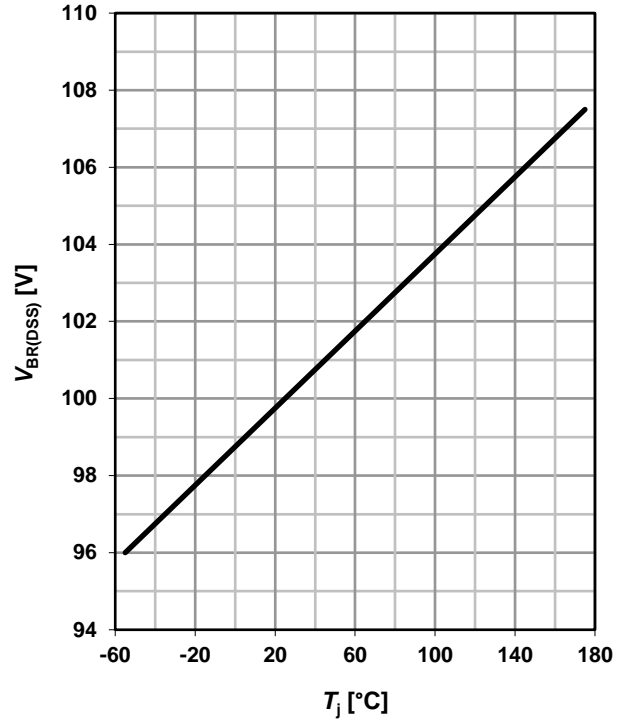
$$E_{AS} = f(T_j)$$

parameter:  $I_D$



**14 Drain-source breakdown voltage**

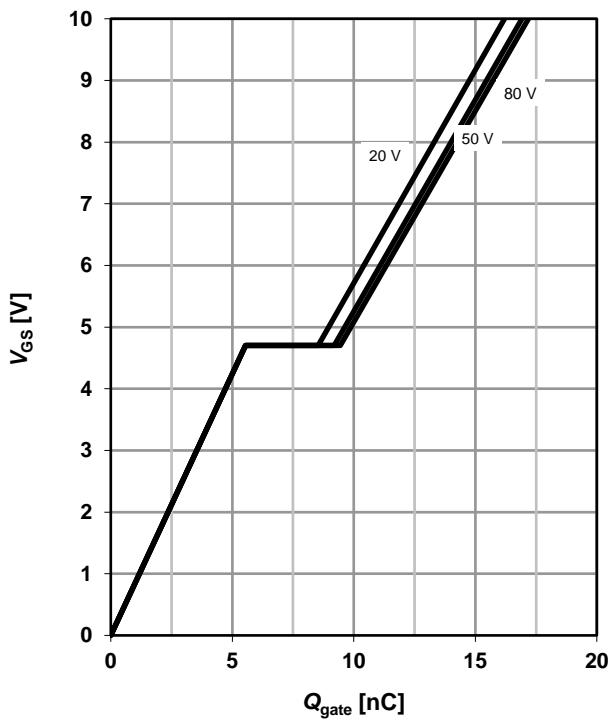
$$V_{BR(DSS)} = f(T_j); I_D = 1 \text{ mA}$$



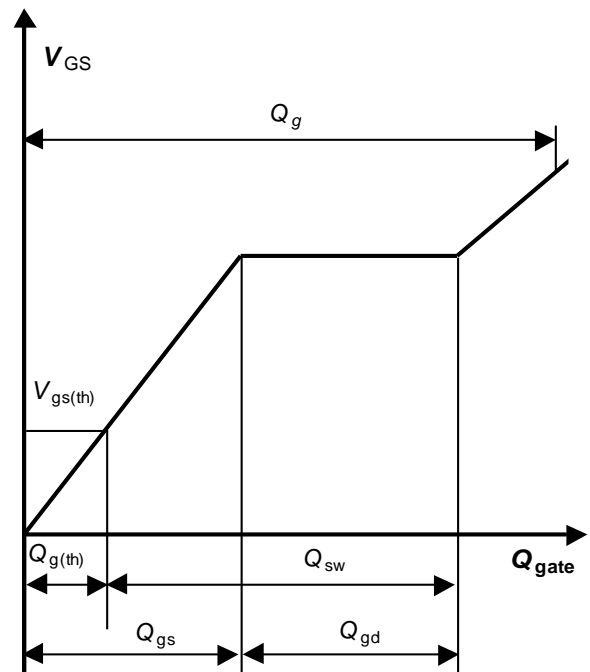
**15 Typ. gate charge**

$$V_{GS} = f(Q_{gate}); I_D = 20 \text{ A pulsed}$$

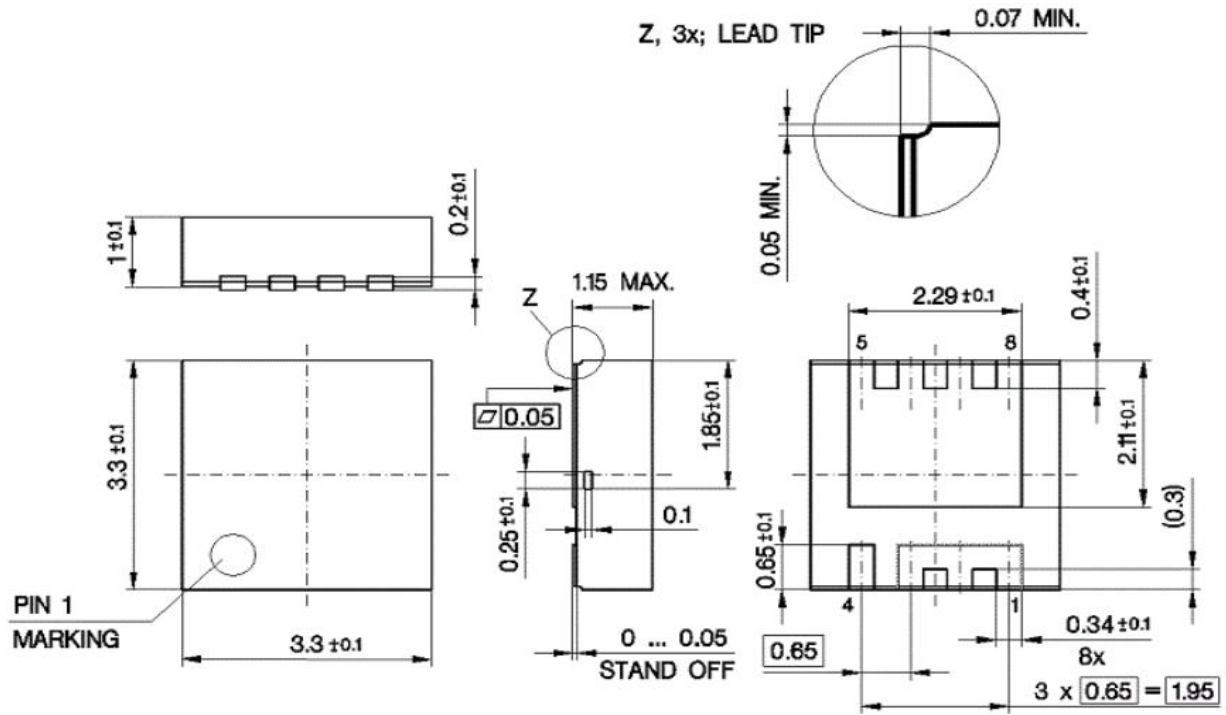
parameter:  $V_{DD}$



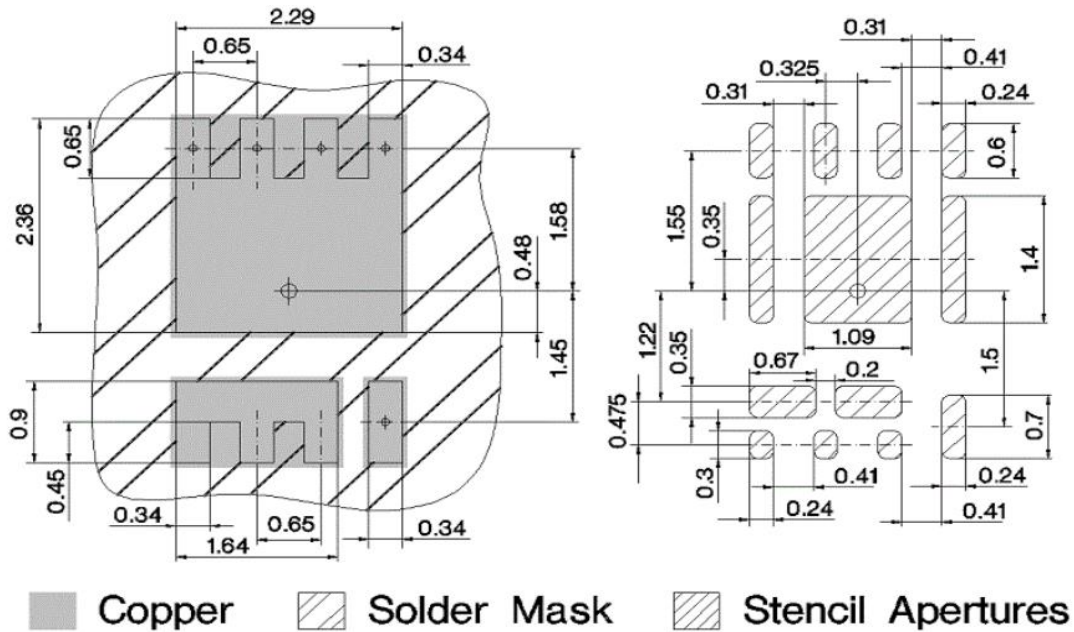
**16 Gate charge waveforms**



PG-TSDSON-8: Outline

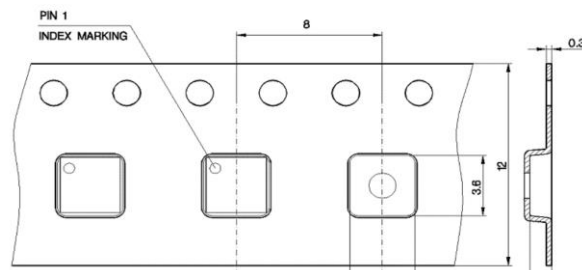


Footprint



Dimensions in mm

Packaging





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Revision History

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| Version      | Date       | Changes          |
|--------------|------------|------------------|
| Revision 1.0 | 23.07.2019 | Final Data Sheet |

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